

RZ/T2H Reference device: Reset
General Description

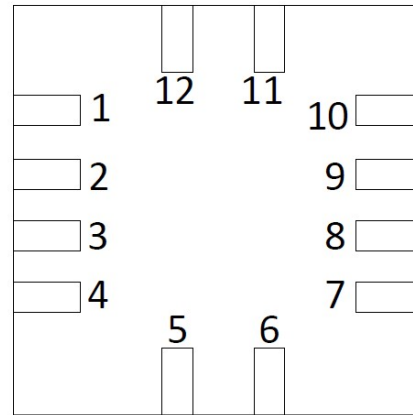
Renesas SLG7RN46360 is a low power and small form device. The SoC is housed in a 1.6mm x 1.6mm STQFN package which is optimal for using with small devices.

Features

- Low Power Consumption
- Pb - Free / RoHS Compliant
- Halogen - Free
- STQFN - 12 Package

Output Summary

2 Outputs - Open Drain NMOS 1X

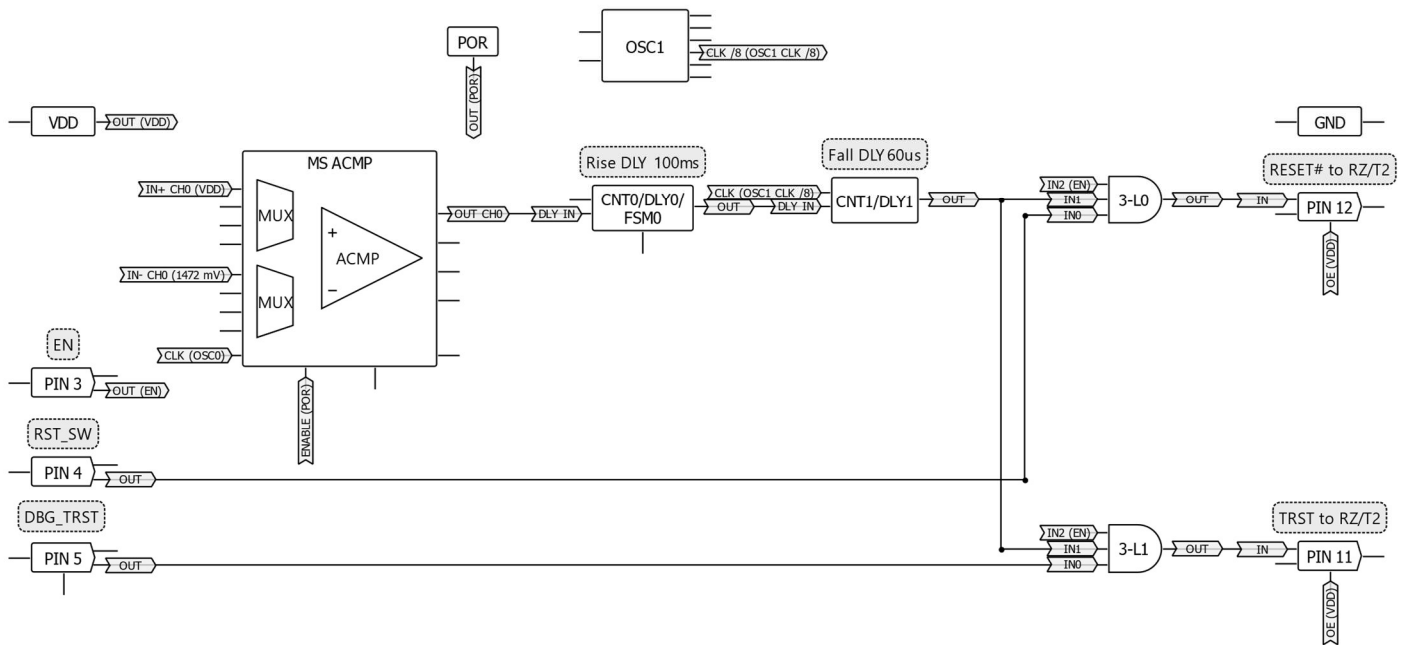
Pin Configuration


**STQFN-12
(Top View)**

Pin name

Pin #	Pin name	Pin #	Pin name
1	VDD	7	GND
2	NC	8	NC
3	EN	9	NC
4	RST_SW	10	NC
5	DBG_TRST	11	TRST to RZ/T2
6	NC	12	RESET# to RZ/T2

Block Diagram



Pin Configuration

Pin #	Pin Name	Type	Pin Description	Internal Resistor
1	VDD	PWR	Supply Voltage	--
2	NC	--	Keep Floating or Connect to GND	--
3	EN	Digital Input	Digital Input without Schmitt trigger	floating
4	RST_SW	Digital Input	Digital Input without Schmitt trigger	floating
5	DBG_TRST	Digital Input	Digital Input without Schmitt trigger	1MΩ pulldown
6	NC	--	Keep Floating or Connect to GND	--
7	GND	GND	Ground	--
8	NC	--	Keep Floating or Connect to GND	--
9	NC	--	Keep Floating or Connect to GND	--
10	NC	--	Keep Floating or Connect to GND	--
11	TRST to RZ/T2	Digital Output	Open Drain NMOS 1X	floating
12	RESET# to RZ/T2	Digital Output	Open Drain NMOS 1X	floating

Ordering Information

Part Number	Package Type
SLG7RN46360V	12-pin STQFN
SLG7RN46360V	12-pin STQFN - Tape and Reel (3k units)

Absolute Maximum Conditions

Parameter		Min.	Max.	Unit
V _{HIGH} to GND		-0.3	7	V
Voltage at Input Pin		GND-0.5V	V _{DD} +0.5V	V
Maximum Average or DC Current (Through V _{DD} or GND pin)		--	90	mA
Maximum Average or DC Current (Through pin)	OD 1x	--	11	mA
Current at Input Pin		-1.0	1.0	mA
Input leakage Current (Absolute Value)		--	1000	nA
Storage Temperature Range		-65	150	°C
Junction Temperature		--	150	°C
ESD Protection (Human Body Model)		2000	--	V
ESD Protection (Charged Device Model)		1300	--	V
Moisture Sensitivity Level		1		

Electrical Characteristics

Symbol	Parameter	Condition/Note	Min.	Typ.	Max.	Unit
V _{DD}	Supply Voltage		3	3.3	3.6	V
T _A	Operating Temperature		-40	25	85	°C
C _{VDD}	Capacitor Value at VDD		--	0.1	--	μF
C _{IN}	Input Capacitance		--	2.5	--	pF
I _Q	Quiescent Current	Static inputs and floating outputs. PINs 3,4,5 are LOW. (after DLY0 time)	--	42	--	μA
V _O	Maximal Voltage Applied to any PIN in High-Impedance State		--	--	V _{DD} +0.3	V
V _{IH}	HIGH-Level Input Voltage	Logic Input (Note 1)	0.7xV _{DD}	--	V _{DD} +0.3	V
V _{IL}	LOW-Level Input Voltage	Logic Input (Note 1)	GND-0.3	--	0.3xV _{DD}	V
V _{OL}	LOW-Level Output Voltage	Open Drain NMOS 1X, I _{OL} =3mA, at V _{DD} =3.3V	--	--	0.08	V
I _{OL}	LOW-Level Output Current	Open Drain NMOS 1X, V _{OL} =0.4V, at V _{DD} =3.3V	12.39	--	--	mA
R _{PULL_DOWN}	Internal Pull Down Resistance	Pull down on PIN 5	--	1	--	MΩ
T _{DLY0}	Delay0 Time	At temperature 25°C	97.57	100.34	103.60	ms
		At temperature -40 +85°C	96.74	100.34	109.89	ms
T _{DLY1}	Delay1 Time	At temperature 25°C	59	60	63	μs
		At temperature -40 +85°C	59	60	65	μs
V _{ACMP}	MS ACMP Channel0 Threshold Voltage	Low to High transition, at temperature 25°C	2924	--	2963	mV
		Low to High transition, at temperature -40 +85°C	2910	--	2970	mV
		High to Low transition, at temperature 25°C	2925	--	2963	mV
		High to Low transition, at temperature -40 +85°C	2909	--	2971	mV
T _{SU}	Startup Time	From V _{DD} rising past PON _{THR}	--	1.85	3.42	ms

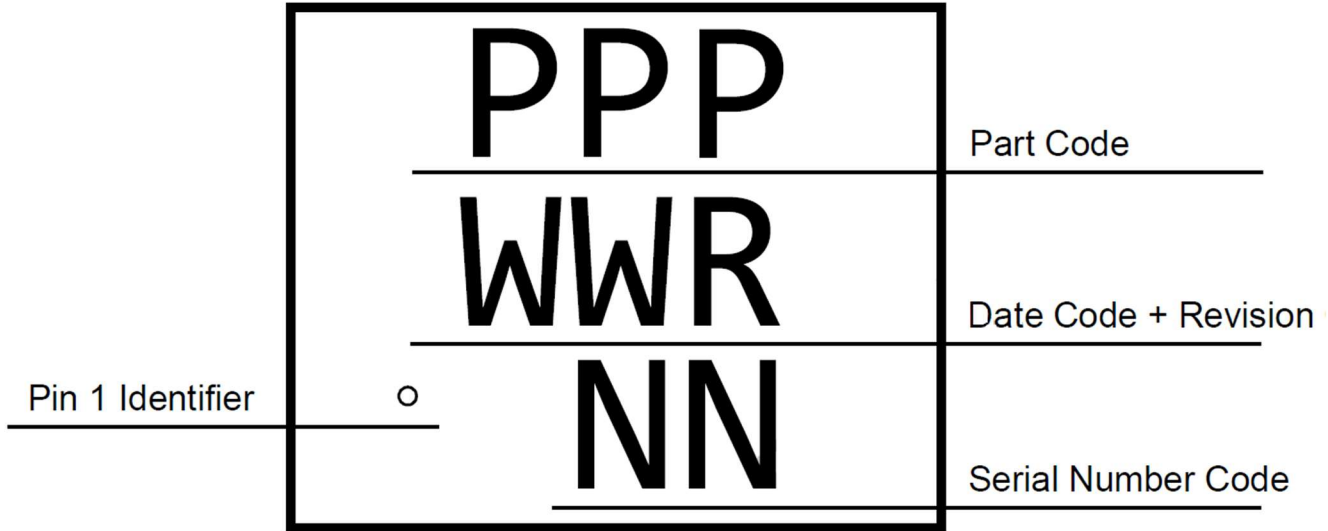
RZ/T2H Reference device: Reset

PON _{THR}	Power On Threshold	V _{DD} Level Required to Start Up the Chip	1.55	1.86	2.17	V
POFF _{THR}	Power Off Threshold	V _{DD} Level Required to Switch Off the Chip	1.06	1.34	1.62	V

Note:

1. No hysteresis.
2. DC or average current through any pin should not exceed value given in Absolute Maximum Conditions.

Package Top Marking



Datasheet Revision	Programming Code Number	Lock Status	Checksum	Part Code	Revision	Date
0.10	001	U	0xAF9C1AEF			03/07/2023

Lock coverage for this part is indicated by \checkmark , from one of the following options:

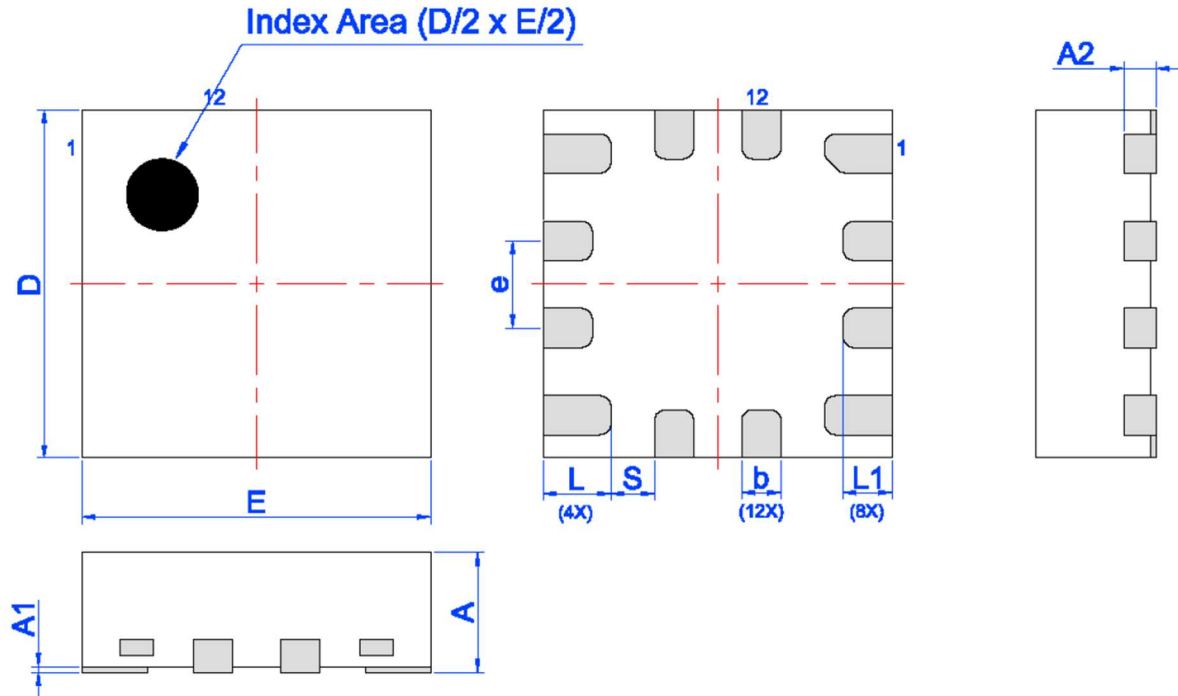
\checkmark	Unlocked
	Partly lock read (mode 1)
	Partly lock read2 (mode 2)
	Partly lock read2/write (mode 3)
	All lock read (mode 4)
	All lock write (mode 5)
	All lock read/write (mode 6)

The IC security bit is locked/set for code security for production unless otherwise specified. The Programming Code Number is not changed based on the choice of locked vs. unlocked status.

Package Outlines

STQFN 12L 1.6 MM X 1.6 MM X 0.55 MM 0.4P FC PACKAGE

IC Net Weight: 0.0035 g



Unit: mm

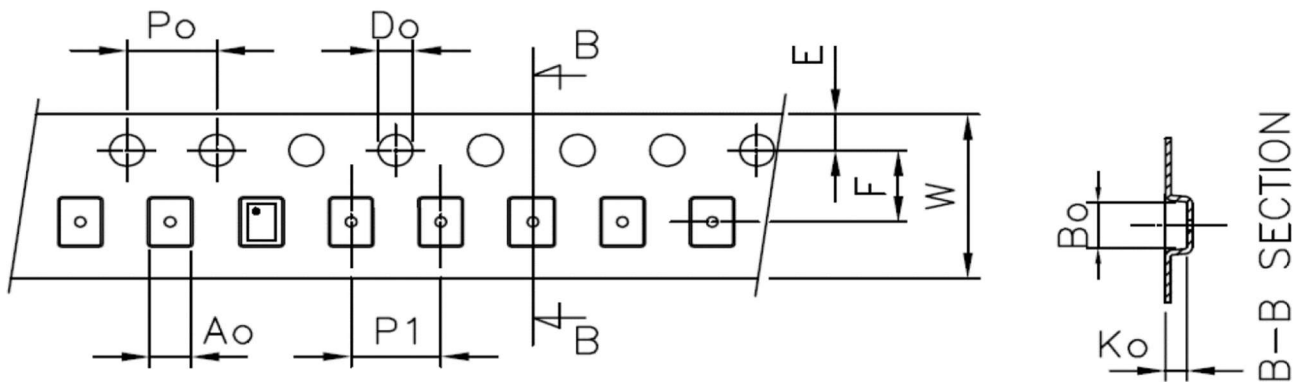
Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
A	0.50	0.55	0.60	D	1.55	1.60	1.65
A1	0.005	-	0.060	E	1.55	1.60	1.65
A2	0.10	0.15	0.20	L	0.26	0.31	0.36
b	0.13	0.18	0.23	L1	0.175	0.225	0.275
e	0.40 BSC			S	0.2 REF		

Tape and Reel Specification

Package Type	# of Pins	Nominal Package Size [mm]	Max Units		Reel & Hub Size [mm]	Leader (min)		Trailer (min)		Tape Width [mm]	Part Pitch [mm]
			per Reel	per Box		Pockets	Length [mm]	Pockets	Length [mm]		
STQFN 12L 1.6mm x 1.6mm x 0.55mm 0.4P FC Green	12	1.6x1.6x0.55	3000	3000	178 / 60	100	400	100	400	8	4

Carrier Tape Drawing and Dimensions


Package Type	Pocket BTM Length	Pocket BTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge	Index Hole to Pocket Center	Tape Width
	A0	B0	K0	P0	P1	D0	E	F	W
STQFN 12L 1.6mm x 1.6mm x 0.55mm 0.4P FC Green	1.8 ± 0.05	1.8 ± 0.05	0.76	4	4	1.5	1.75	3.5	8




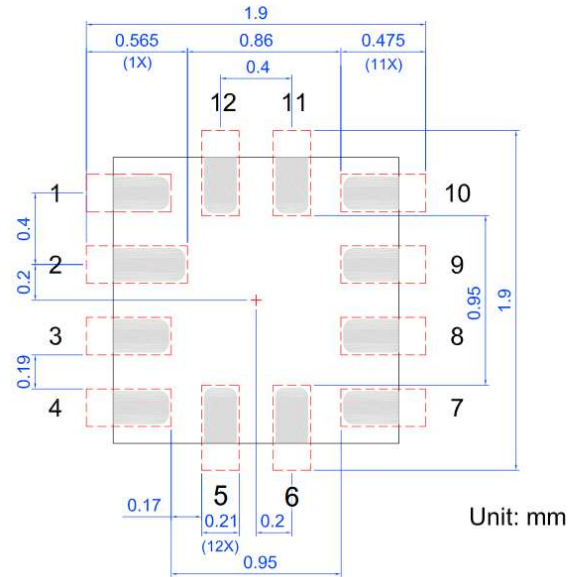
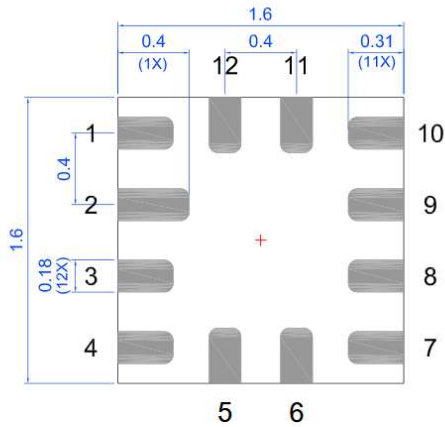
Recommended Reflow Soldering Profile

Please see IPC/JEDEC J-STD-020. More information can be found at www.jedec.org.

Layout Guidelines

Expose Pad 
(Package face down)

Recommended Landing Pattern 
(Package face down)



Datasheet Revision History

Date	Version	Change
03/07/2023	0.10	New design for SLG46811V chip

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